

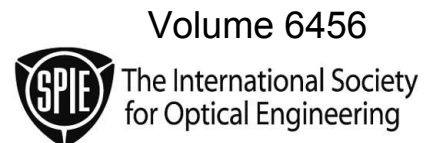
PROCEEDINGS OF SPIE

# ***High-Power Diode Laser Technology and Applications V***

**Mark S. Zediker**  
*Chair/Editor*

**22–24 January 2007**  
**San Jose, California, USA**

*Sponsored and Published by*  
SPIE—The International Society for Optical Engineering



Proceedings of SPIE—The International Society for Optical Engineering, 9780819465696, v. 6456

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Please use the following format to cite material from this book:

Author(s), "Title of Paper," in *High-Power Diode Laser Technology and Applications V*, edited by Mark S. Zediker, Proceedings of SPIE Vol. 6456 (SPIE, Bellingham, WA, 2007) Article CID Number.

ISSN 0277-786X  
ISBN 9780819465696

Published by  
**SPIE—The International Society for Optical Engineering**  
P.O. Box 10, Bellingham, Washington 98227-0010 USA  
Telephone 1 360/676-3290 (Pacific Time) · Fax 1 360/647-1445  
<http://www.spie.org>

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Printed in the United States of America.

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